# Switch-mode Dual Schottky Power Rectifier

### Features and Benefits

- Highly Stable Oxide Passivated Junction
- Very Low Forward Voltage Drop (0.4 Max @ 10 A,  $T_C = 150^{\circ}C$ )
- High Junction Temperature
- High dv/dt Capability
- Excellent Ability to Withstand Reverse Avalanche Energy Transients
- Low Power Loss/High Efficiency
- High Surge Capacity
- 175°C Operating Junction Temperature
- 20 A Total (10 A Per Diode Leg)
- This Device is Pb-Free and is RoHS Compliant\*

### Applications

- Power Supply Output Rectification
- Power Management ORING
- Instrumentation

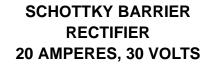
### **Mechanical Characteristics**

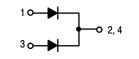
- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Sec
- ESD Rating: Human Body Model 3B Machine Model C



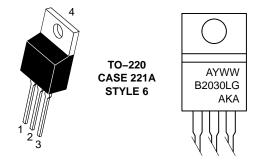
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#### MARKING DIAGRAM



А	= Assembly Location
Y	= Year
WW	= Work Week
B2030L	= Device Code
G	= Pb–Free Package
AKA	= Diode Polarity

#### **ORDERING INFORMATION**

Device	Package	Shipping
MBR2030CTLG	TO-220 (Pb-Free)	50 Units/Rail

\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### MAXIMUM RATINGS (Per Leg)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	30	V
Average Rectified Forward Current $(T_C = 167^{\circ}C)$ Per Diode Per Device	I <sub>F(AV)</sub>	10 20	A
Non-repetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I <sub>FSM</sub>	150	A
Peak Repetitive Forward Current (Square Wave, 20 kHz, $T_C = 166^{\circ}C$ )	I <sub>FRM</sub>	10	A
Peak Repetitive Reverse Surge Current (2.0 µs, 1.0 kHz)	I <sub>RRM</sub>	1.0	А
Operating Junction Temperature (Note 1)	TJ	-65 to +175	°C
Storage Temperature	T <sub>stg</sub>	-65 to +175	°C
Voltage Rate of Change (Rated V <sub>R</sub> )	dv/dt	1000	V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. The heat generated must be less than the thermal conductivity from Junction–to–Ambient:  $dP_D/dT_J < 1/R_{\theta JA}$ .

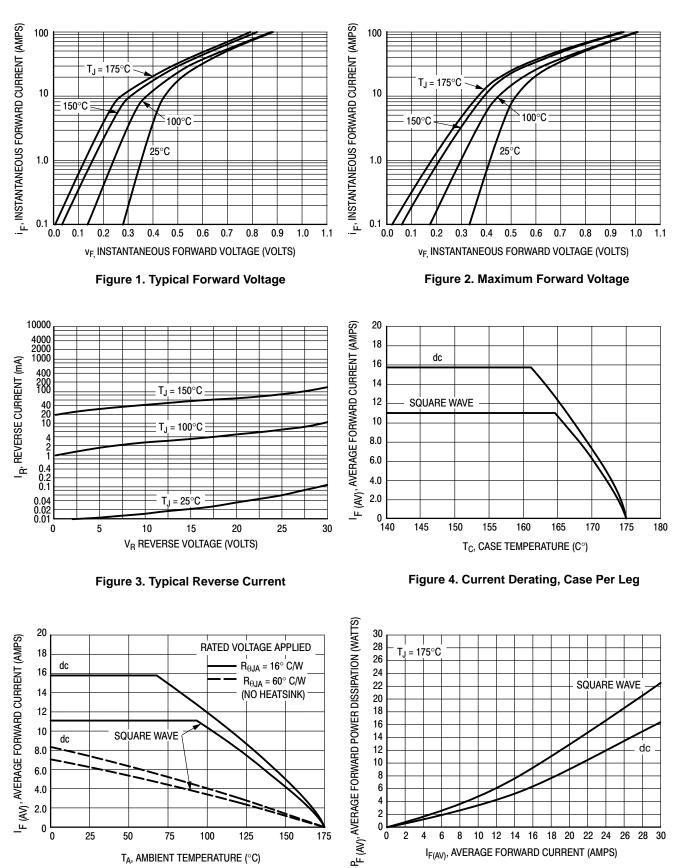
#### THERMAL CHARACTERISTICS (Per Leg)

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance, Junction-to-Case (Min. Pad)	$R_{ extsf{ heta}JC}$	2.0	°C/W
Maximum Thermal Resistance, Junction-to-Ambient (Min. Pad)	$R_{\thetaJA}$	60	°C/W

#### ELECTRICAL CHARACTERISTICS (Per Leg)

Characteristic	Symbol	Min	Тур	Max	Unit
$ \begin{array}{l} \mbox{Maximum Instantaneous Forward Voltage (Note 2)} \\ (i_F = 10 \mbox{ Amps, } T_J = 25^{\circ}C) \\ (i_F = 10 \mbox{ Amps, } T_J = 150^{\circ}C) \\ (i_F = 20 \mbox{ Amps, } T_J = 25^{\circ}C) \\ (i_F = 20 \mbox{ Amps, } T_J = 150^{\circ}C) \end{array} $	VF		0.45 0.32 0.51 0.41	0.52 0.40 0.58 0.48	V
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, $T_J = 25^{\circ}$ C) (Rated dc Voltage, $T_J = 100^{\circ}$ C) (Rated dc Voltage, $T_J = 125^{\circ}$ C)	i <sub>R</sub>		0.11 10 -	5.0 40 75	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Pulse Test: Pulse Width = 5.0 ms, Duty Cycle  $\leq 10\%$ .



T<sub>A</sub>, AMBIENT TEMPERATURE (°C)

Figure 5. Current Derating, Ambient Per Leg

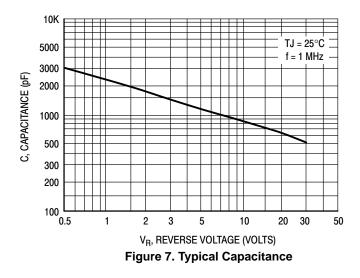
**Figure 6. Forward Power Dissipation** 

IF(AV), AVERAGE FORWARD CURRENT (AMPS)

10 12 14 16 18 20 22 24

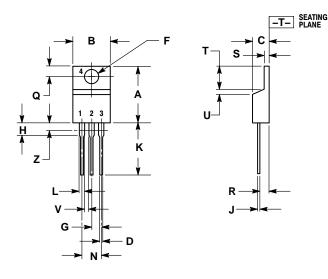
26 28 30

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#### PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AH** 



NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

3 DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED

	INC	HES	MILLIMETER	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
κ	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
Ν	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
۷	0.045		1.15	
Ζ		0.080		2.04

STYLE 6: PIN 1. ANODE 2. CATHODE ANODE 3. CATHODE

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